



RoHS

COMPLIANT

HALOGEN

FREE

300 MHz, 2.5 Ω , Dual SPDT Analog Switches

DESCRIPTION

The DG3516, DG3517 are dual SPDT analog switches which operate from 1.8 V to 5.5 V single rail power supply. They are design for audio, video, and USB switching applications.

The devices have 2.5 Ω on-resistance and 300 MHz 3dB bandwidth. 0.2 Ω on-resistance matching and 1 Ω flatness make the device high linearity. The devices are 1.6 V logic compatible within the full operation voltage range.

These switches are built on a sub-micron high density process that brings low power consumption and low voltage performance.

The switches are packaged in MICRO FOOT chip scale package of 4 mm x 3 mm bump array.

As a committed partner to the community and environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switch products manufactured with tin/silver/copper (SnAgCu) device termination, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- 1.8 V to 5.5 V operation
- 2.5Ω at $2.7 V R_{ON}$
- 300 MHz 3 dB bandwidth
- ESD method 3015.7 > 2 kV
- Latch-up current 200 mA (JESD 78)
- 1.6 V logic compatible
- Compliant to RoHS Directive 2002/95/EC

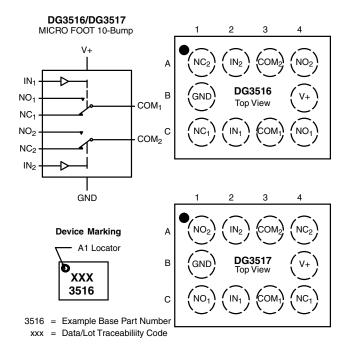
BENEFITS

- Space Saving MICRO FOOT® Package
- **High Linearity**
- Low Power Consumption
- High Bandwidth
- Full Rail Signal Swing Range

APPLICATIONS

- Cellular Phones
- MP3
- Media Players
- Modems
- Hard Drives
- **PCMCIA**

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE							
Logic	NC1 and NC2	NO1 and NO2					
0	ON	OFF					
1	OFF	ON					

ORDERING INFORMATION								
Temp. Range	Package	Part Number						
- 40 °C to 85 °C	MICRO FOOT: 10 Bump (4 x 3, 0.5 mm Pitch, 238 µm Bump Height)	DG3516DB-T5-E1 DG3517DB-T5-E1						

Document Number: 73404 S11-1185-Rev. D, 13-Jun-11

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ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference V+ to GND	- 0.3 to + 6	V				
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	V			
Continuous Current (NO, NC, COM)		± 100	mA			
Peak Current (Pulsed at 1 ms, 10 % du	ty cycle)	± 200	IIIA			
Storage Temperature	(D Suffix)	- 65 to 150	00			
Package Solder Reflow Conditions ^b	250	°C				
ESD per Method 3015.7	> 2	kV				
Power Dissipation (Packages) ^c	MICRO FOOT: 10 Bump (4 mm x 3 mm) ^d	457	mW			

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. Refer to IPC/JEDEC (J-STD-020B).
- c. All bumps welded or soldered to PC board.
- d. Derate 5.7 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 3 V)									
		Test Conditions Otherwise Unless Specified			Limits - 40 °C to 85 °C				
Parameter	Symbol	V+ = 2.7 V to 3.6 V	$V_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^e$	Temp.a	Min.b	Typ. ^c	Max.b	Unit	
Analog Switch									
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}			Full	0		V+	٧	
On-Resistance ^d	R _{ON}	V+ = 2.7 V I _{NO} , I _{NC} = 10 mA	V _{COM} = 1.5 V	Room Full		2.5	3.5 3.8		
R _{ON} Flatness ^d	R _{ON} Flatness		V _{COM} = 1, 1.5, 2 V	Room		0.52	1	Ω	
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		V _{COM} = 1.5 V	Room			0.25		
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}		= 3.3 V,	Room Full	- 2 - 20		2 20		
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 0.3 \text{ V/3 V}$, $V_{COM} = 3 \text{ V/0.3 V}$		Room Full	- 2 - 20		2 20	nA	
Channel-On Leakage Current	I _{COM(on)}	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V/3 V}$		Room Full	- 2 - 20		2 20		
Digital Control									
Input High Voltage ^d	V_{INH}			Full	1.4			V	
Input Low Voltage	V _{INL}			Full			0.5] '	
Input Capacitance	C _{in}			Full		5		pF	
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$	V or V+	Full	1		1	μΑ	



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SPECIFICATIONS (V+ = 3 V)								
		Test Conditions Otherwise Unless Specified			- 40	Limits O °C to 85	5 °C	
Parameter	Symbol	V+ = 2.7 V to 3.6 V, V	$I_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^{e}$	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Dynamic Characteristics								
Turn-On Time	t _{ON}	V 27 V V	V+ = 2.7 V, V_{NO} or V_{NC} = 1.5 V R_L = 300 Ω, C_L = 35 pF			21	51 52	
Turn-Off Time	t _{OFF}					15	45 46	ns
Break-Before-Make Time	t _d				1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 2 \text{ V, } R_{GEN} = 0 \Omega$		Room		1		рC
Off Is also you	OIRR		f = 1 MHz	Room		- 74		
Off-Isolation ^d	Oinn	$R_{L} = 50 \Omega, C_{L} = 5 pF$	f = 10 MHz	Room		- 54		dB
Crosstalk ^d	X _{TALK}	11 <u>1</u> = 00 32, 0 <u>1</u> = 0 pi	f = 1 MHz	Room		- 76		ub
Crossiaik	MALK		f = 10 MHz	Room		- 56		
N. N. Off Consoiteneed	C _{NO(off)}			Room		12		
N _O , N _C Off Capacitance ^d	C _{NC(off)}	\/ -0 or \/.	V _{IN} = 0 or V+, f = 1 MHz			12		
O. 1000 d	C _{NO(on)}	V _{IN} = 0 01 V+				40		pF
Channel-On Capacitance ^d	C _{NC(on)}			Room		40		
Power Supply	<u> </u>			•			•	
Power Supply Current	l+	V _{IN} = 0 \	/ or V+	Room Full			1 1	μА

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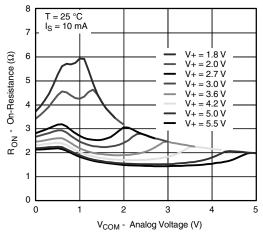


		Test Conditions Otherwise Unless Specified $V+ = 4.2 \text{ V to } 5.5 \text{ V}, V_{\text{IN}} = 0.8 \text{ V or } 2 \text{ V}^{\text{e}}$			Limits - 40 °C to 85 °C			
Parameter	Symbol			Temp.a	Min.b	Typ.c	Max.b	Unit
Analog Switch								
Analog Signal Range ^d	V_{NO}, V_{NC}, V_{COM}			Full	0		V+	٧
On-Resistance ^d	R _{ON}		V _{COM} = 3.5 V	Room Full		2.2	2.9 3.1	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 4.2 V I_{NO} , $I_{NC} = 10 \text{ mA}$	V _{COM} = 1, 2, 3.5 V	Room		0.53	1	Ω
On-Resistance Match Between Channels ^d	$\Delta R_{DS(on)}$		V _{COM} = 3.5 V	Room			0.25	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}		5.5 V,	Room Full	- 2 - 20		2 20	
Switch On Leakage Current	I _{COM(off)}	$V_{NO}, V_{NC} = 1 \text{ V}/4.5$	5 V, V _{COM} = 4.5 V/1 V	Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current	I _{COM(on)}	$V+ = 5.5 V, V_{NO}, V_{NO}$	$_{IC} = V_{COM} = 1 \text{ V/4.5 V}$	Room Full	- 2 - 20		2 20	
Digital Control								
Input High Voltage ^d	V_{INH}				2			V
Input Low Voltage	V _{INL}						0.8	•
Input Capacitance	C _{in}			Full		5		pF
Input Current	I _{INL} or I _{INH}	V _{IN} =	0 or V+	Full	1		1	μΑ
Dynamic Characteristics								
Turn-On Time	t _{ON}	V+ = 4 2 V V	NO or V _{NC} = 3 V	Room Full		15	45 46	
Turn-Off Time	t _{OFF}	•	$C_{L} = 35 \text{ pF}$	Room Full		12	42 43	ns
Break-Before-Make Time	t _d			Full	1			
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN}$	= 2 V, R_{GEN} = 0 Ω	Room		1		рС
Off-Isolation ^d	OIRR		f = 1 MHz	Room		- 74		- dB
On-Isolation	U	$R_1 = 50 \Omega$, $C_1 = 5 pF$	f = 10 MHz	Room		- 54		
Crosstalk ^d	X _{TALK}		f = 1 MHz	Room		- 78		
	C		f = 10 MHz	Room		- 56	-	
N _O , N _C Off Capacitance ^d	C _{NO(off)}			Room		12	 	pF
	C _{NC(off)}	V _{IN} = 0 or \	/+, f = 1 MHz	Room		12		
Channel-On Capacitanced	C _{NO(on)}	4		Room		40	 	1
Power Supply	C _{NC(on)}			Room		40	<u> </u>	
Power Supply Current	I+	$V_{IN} = 0$) V or V+	Room Full			1 1	μA

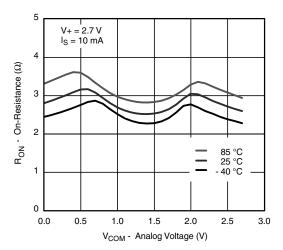
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V testing, not production tested.

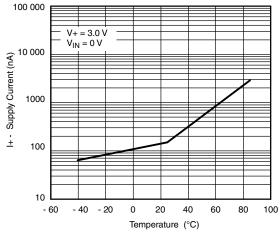
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



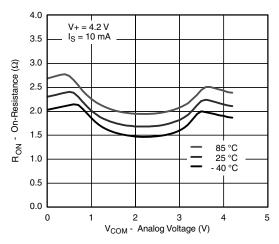
R_{ON} vs. V_{COM} and Single Supply Voltage



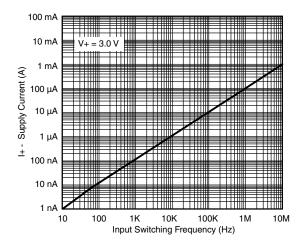
R_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Temperature



R_{ON} vs. Analog Voltage and Temperature

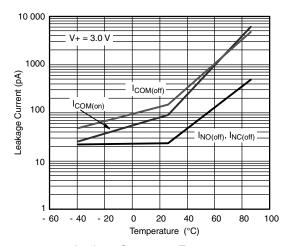


Supply Current vs. Input Switching Frequency

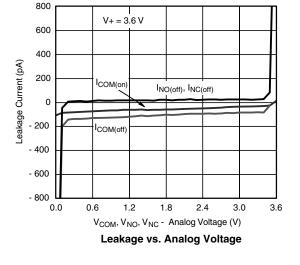
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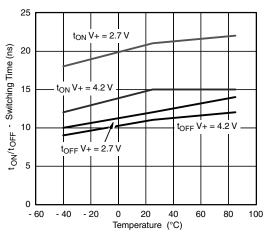
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

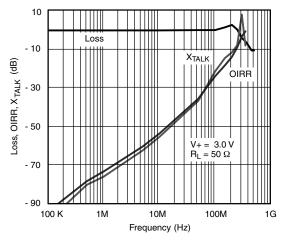


Leakage Current vs. Temperature

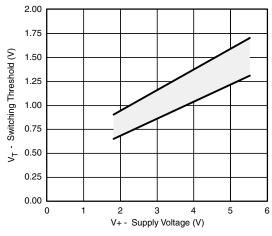




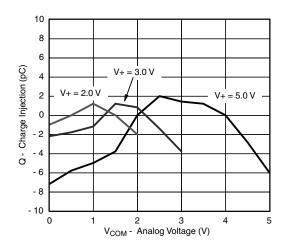
Switching Time vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency

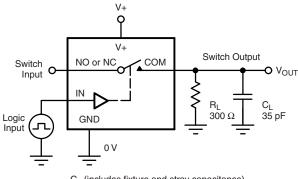


Switching Threshold vs. Supply Voltage



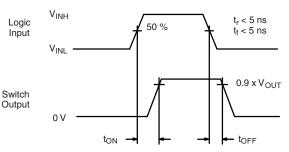
Charge Injection vs. Analog Voltage

TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

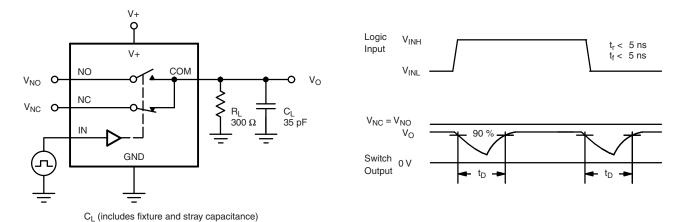
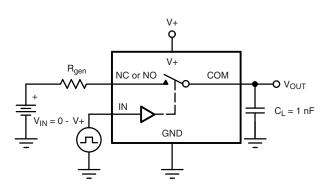
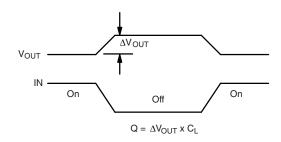


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

TEST CIRCUITS



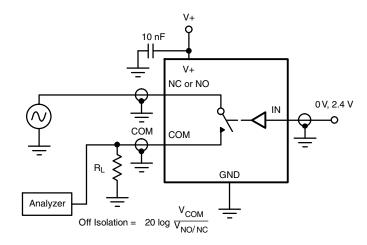


Figure 4. Off-Isolation

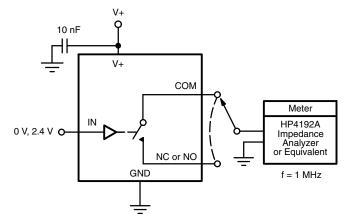
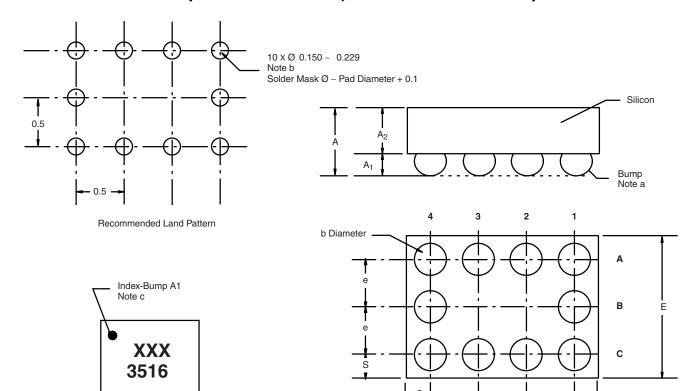


Figure 5. Channel Off/On Capacitance



PACKAGE OUTLINE

MICRO FOOT: 10 BUMP (4 x 3 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

- a. Bump is Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.

Top Side (Die Back)

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

Dim.	Millimeters ^a		Inc	hes
	Min.	Max.	Min.	Max.
A	0.688	0.753	0.0271	0.0296
A ₁	0.218	0.258	0.0086	0.0102
A ₂	0.470	0.495	0.0185	0.0195
b	0.306	0.346	0.0120	0.0136
D	1.980	2.020	0.0780	0.0795
E	1.480	1.520	0.0583	0.0598
е	0.5 BASIC		0.0197	BASIC
S	0.230	0.270	0.0091	0.0106

Notes:

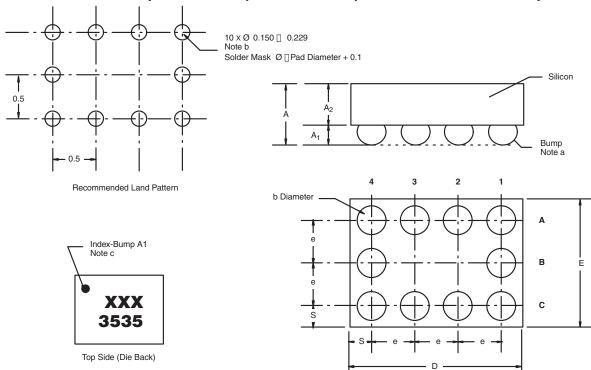
a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73404.

Document Number: 73404 S11-1185-Rev. D, 13-Jun-11



MICRO FOOT: 10-BUMP (4 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes

(unless otherwise specified)

- a. Bump is lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

DIM.	MILLIMETERS ^a		INC	HES	
	MIN.	MAX.	MIN.	MAX.	
Α	0.688	0.753	0.0271	0.0296	
A ₁	0.218	0.258	0.0086	0.0102	
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Е	1.480	1.520	0.0583	0.0598	
е	0.5 BASIC		0.0197	BASIC	
S	0.230	0.270	0.0091	0.0106	

a. Use millimeters as the primary measurement.

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